

AMP5030P SOLID STATE HIGH POWER AMPLIFIER

FEATURES

Class A/AB linear LDMOS design
Compact Small form factor, light weight, high power density
Dual stage Driver, 3dB Divider, Final power amplifiers
Suitable for L-Band pulse applications
Built-in monitoring and protection circuits
High reliability and ruggedness



ELECTRICAL SPECIFICATIONS

Parameter	Specification			Notes
Operating Frequency Range	1030 MHz			
Internal assemblies	Output 1 CW	Input 2 Pulsed	Output 2 Pulsed	
Power Output @ Pulse	300 mW	100 mW	65 Watt	Peak pulse
Power Gain	15 dB	N/A	28 dB Min	
Pulse Characteristics	Width	Duty Cycle	PRF	
		10 - 20 %	100 - 400 KHz	
Input Power for rated output	+10 dBm Nom			
Input Return Loss	-10 dB Max			
Harmonics 2 nd / 3 rd	-30 dBc Max			At rated Pout
Spurious	-60 dBc Max			Non-harmonics
Operating Voltage	28- 30 VDC Nom			
Current Consumption	2 Amp Ave. / 6 Amp Peak Max			At rated Pout
Input Power Protection	+16 dBm Max			<10 Sec without damage
Load VSWR Protection	∞ : 1 ¹ Max			<1 minute at rated Pout
Turn On / Off Speed	5 μ Sec Max			

1 Modules could be damaged due to excessive VSWR beyond 1 minute

ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Notes
Operating Case Temperature	-20 to +75 °C	
Storage Temperature	-40 to +85 °C	
Relative Humidity	up to 95 %	Non-condensing
Altitude	3000 meters	
Shock & Vibration	Normal transport ²	

2 MIL Spec available for quotation

MECHANICAL SPECIFICATIONS

Parameter	Specification	Notes
Dimensions	220 x 120 x 38 mm	Excluding connectors
Weight	1440 gr.	
RF Connectors In/Out	SMA female	
DC Power / Interface Connector	9-Pin D-Sub	
Cooling	External Heatsink	Forced air required

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